

2SB647(A)

Rev.E Mar.-2016

KF 50) CD

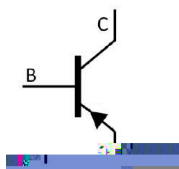
GE G

Silicon PNP transistor in a TO-92LM Plastic Package.

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Complementary pair with 2SD667(A).

Low frequency power amplifier.



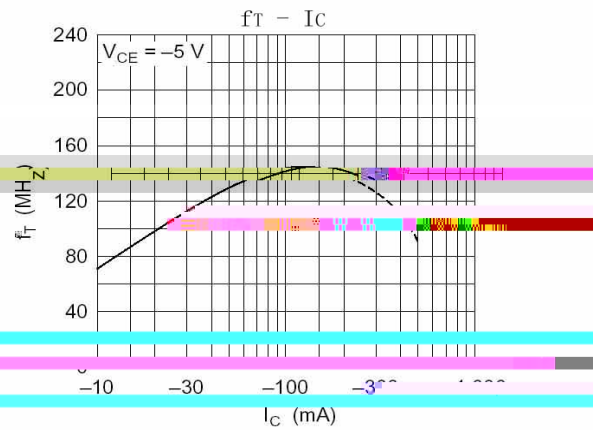
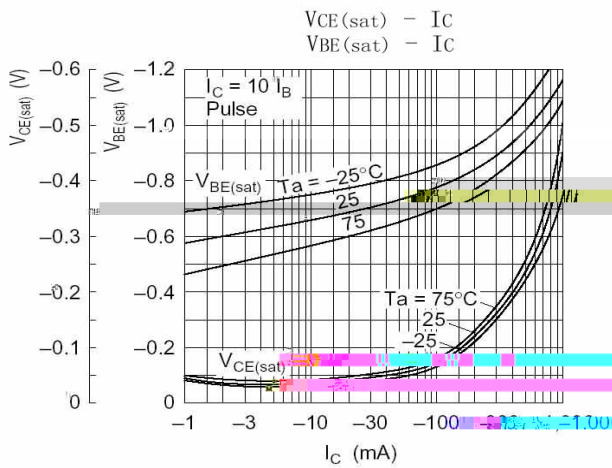
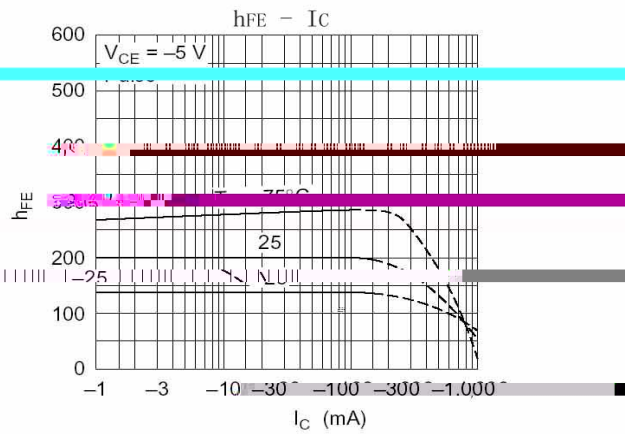
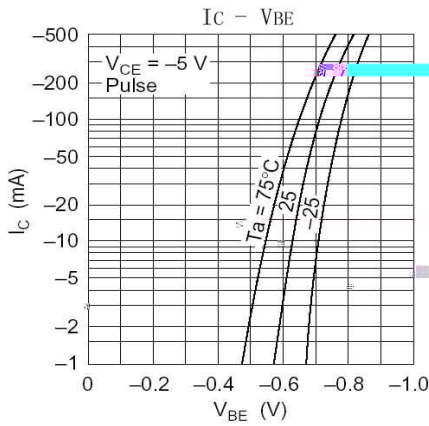
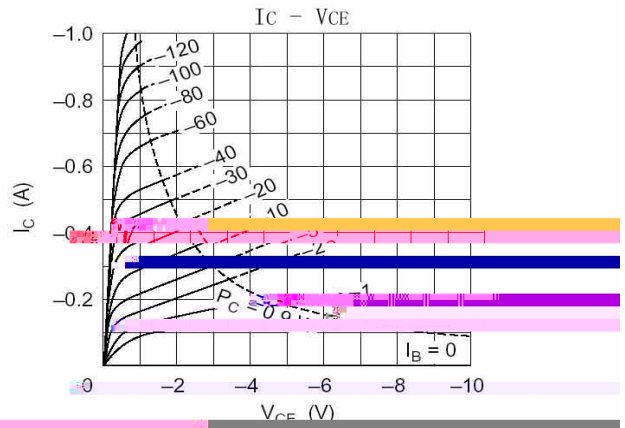
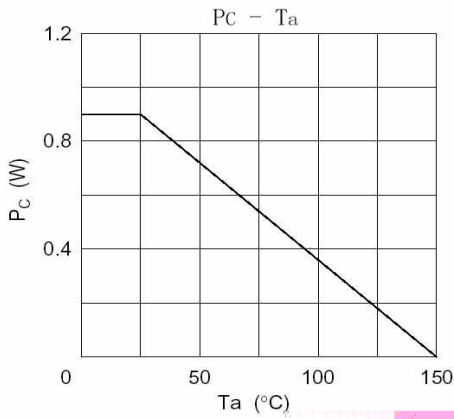
PIN1 Base

PIN 2 Collector

PIN 3 Emitter

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-120	V
Collector to Emitter Voltage	V_{CEO}	2SB647	-80
		2SB647A	-100
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current (DC)	I_C	-1.0	A
Collector Current(Pulse)	I_{CP}	-2.0	A
Collector Power Dissipation	P_C	900	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T		

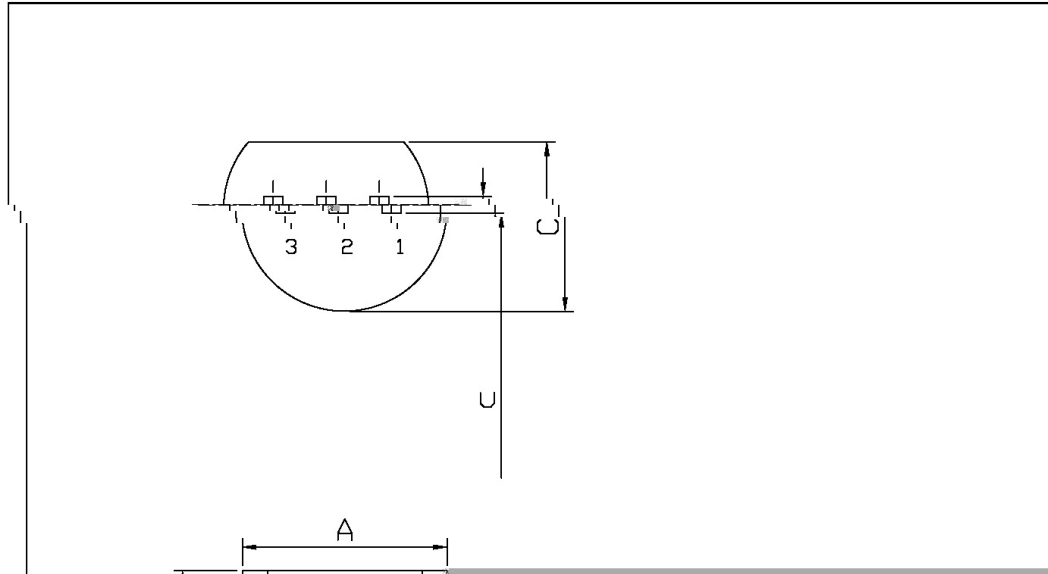
/ Electrical Characteristic Curve



/ Package Dimensions

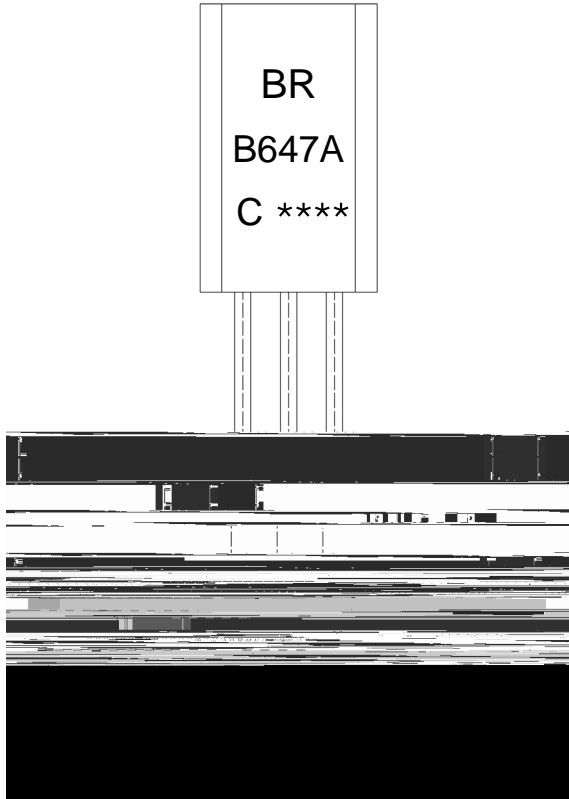
TO-92LM

Unit: mm



Symbol	Dimensions In Millimeters	
	Min	Max
A	4.47	5.1
C	4.2	4.8
U	1.2	1.6
Lead 1 length	0.5	0.8
Lead 2 length	0.5	0.8
Lead 3 length	0.5	0.8
Lead 1 angle	15°	15°
Lead 2 angle	15°	15°
Lead 3 angle	15°	15°
Lead 1 thickness	0.1	0.15
Lead 2 thickness	0.1	0.15
Lead 3 thickness	0.1	0.15
Lead 1 pitch	0.5	0.5
Lead 2 pitch	0.5	0.5
Lead 3 pitch	0.5	0.5
Lead 1 diameter	0.1	0.15
Lead 2 diameter	0.1	0.15
Lead 3 diameter	0.1	0.15
Lead 1 length to body	0.5	0.8
Lead 2 length to body	0.5	0.8
Lead 3 length to body	0.5	0.8
Lead 1 angle to body	15°	15°
Lead 2 angle to body	15°	15°
Lead 3 angle to body	15°	15°
Lead 1 thickness to body	0.1	0.15
Lead 2 thickness to body	0.1	0.15
Lead 3 thickness to body	0.1	0.15
Lead 1 pitch to body	0.5	0.5
Lead 2 pitch to body	0.5	0.5
Lead 3 pitch to body	0.5	0.5
Lead 1 diameter to body	0.1	0.15
Lead 2 diameter to body	0.1	0.15
Lead 3 diameter to body	0.1	0.15

/ Marking Instructions

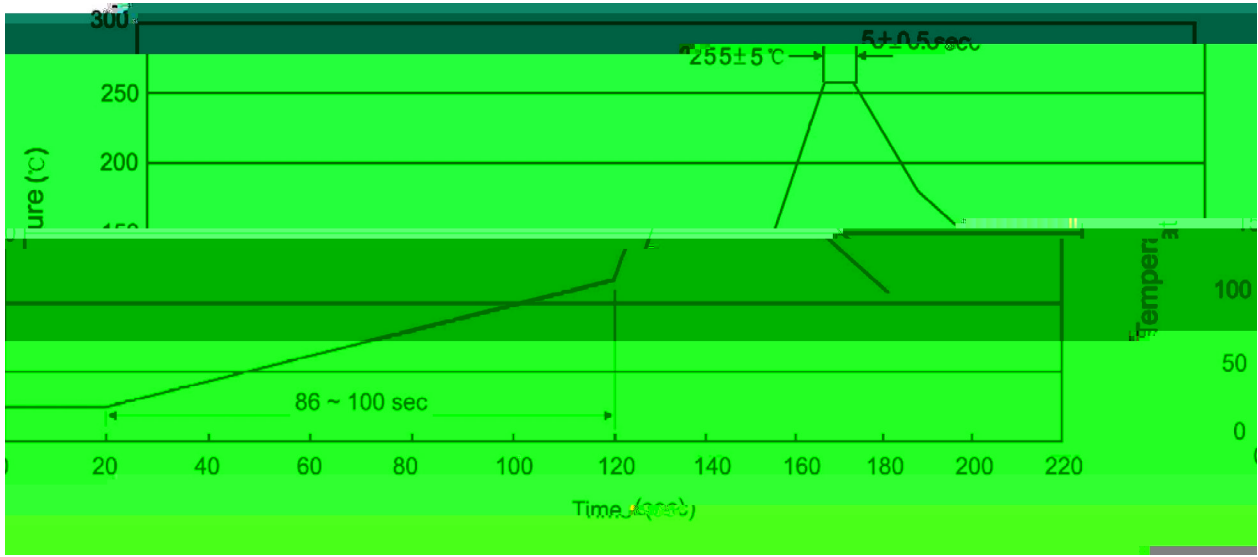


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Note:

- BR: Company Code.
- B647A: Product Type.
- C: h_{FE} Classifications Symbol
- ****: Lot No. Code,code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

1 25 150 60 90sec;

1.Preheating:25~150